

N-channel TrenchMOS standard level FET

Rev. 2 — 2 February 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

| | Guick reference ua | ta | | | | |
|----------------------|----------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 100 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u> | - | - | 63 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 200 | W |
| Static cha | racteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | - | 50 | mΩ |
| | | V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 17 | 20 | mΩ |
| Avalanche | e ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $ \begin{split} I_D &= 60 \text{ A}; \text{V}_{\text{sup}} \leq 100 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $ | - | - | 400 | mJ |

Suitable for standard level gate drive sources

Suitable for thermally demanding environments due to 175 °C rating

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Motors, lamps and solenoids

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2. Pinning information

| Table 2. | Pinning information | | | |
|----------|---------------------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | - |
| 2 | D | drain | mb | |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | SOT404 (D2PAK) | |

3. Ordering information

| Table 3. Ordering information | | | | | | |
|-------------------------------|---------|-------------------------------------------------------------------------------------|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| BUK7620-100A | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 | | | |

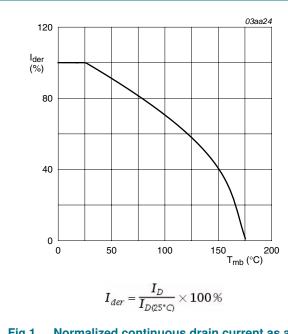
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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Мах | Unit |
|----------------------|-------------------------------------------------|----------------------------------------------------------------------------------------------------------|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 100 | V |
| V _{DGR} | drain-gate voltage | R _{GS} = 20 kΩ | - | 100 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u> | - | 63 | А |
| | | T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u> | - | 44 | А |
| I _{DM} | peak drain current | T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u> | - | 253 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 200 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| Source-drain | diode | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 63 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 253 | А |
| Avalanche rug | ggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 60 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped | - | 400 | mJ |





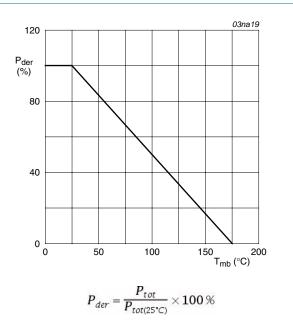
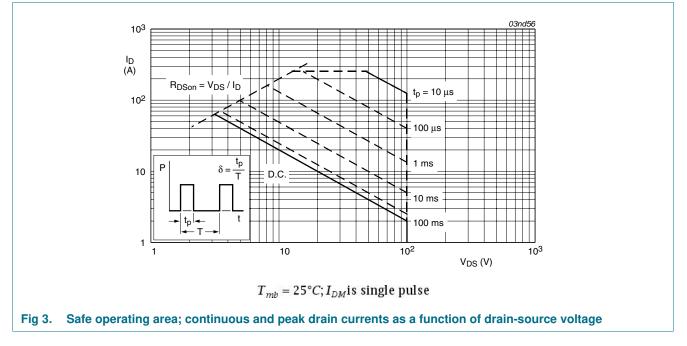


Fig 2. Normalized total power dissipation as a function of mounting base temperature

BUK7620-100A

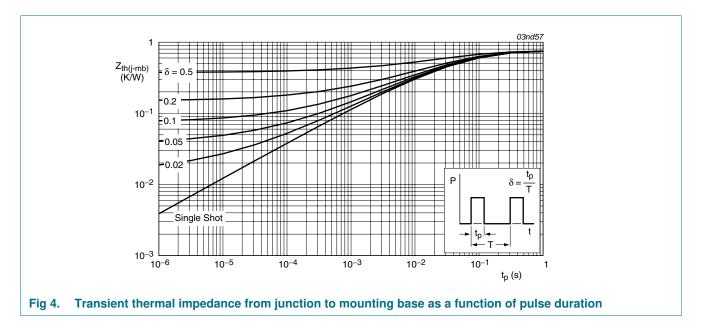
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5. Thermal characteristics

Table 5.Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---------------------------------------------------|----------------------------------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <u>Figure 4</u> | - | - | 0.75 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | mounted on a printed-circuit board; minimum footprint | - | 50 | - | K/W |



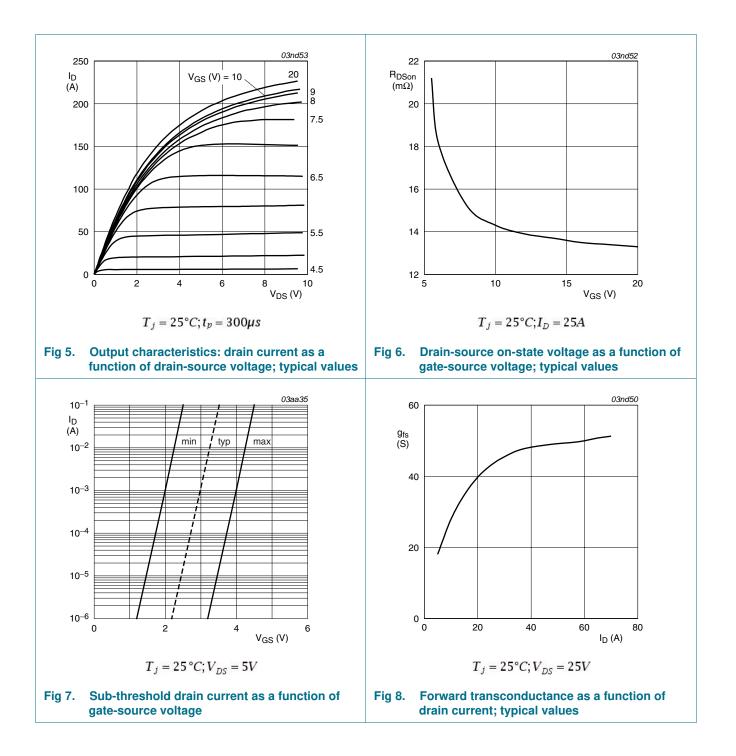
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6. Characteristics

| Table 6. | Characteristics | | | | | |
|----------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C | 100 | - | - | V |
| | breakdown voltage | I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C | 89 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 11</u> | 2 | 3 | 4 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u> | - | - | 4.4 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u> | 1 | - | - | V |
| I _{DSS} | drain leakage current | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.05 | 10 | μA |
| | | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | - | 50 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 17 | 20 | mΩ |
| Dynamic | characteristics | | | | | |
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; | - | 3430 | 4373 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 14</u> | - | 440 | 525 | pF |
| C _{rss} | reverse transfer capacitance | | - | 260 | 352 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 30 V; R_{L} = 1.2 Ω ; V_{GS} = 10 V; | - | 21 | - | ns |
| t _r | rise time | R _{G(ext)} = 10 Ω; T _j = 25 °C | - | 87 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 108 | - | ns |
| t _f | fall time | | - | 56 | - | ns |
| L _D | internal drain inductance | from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$ | - | 2.5 | - | nH |
| | | from drain lead 6 mm from package to centre of die; T _j = 25 °C | - | 4.5 | - | nH |
| L _S | internal source inductance | from source lead to source bond pad; T _j = 25 °C | - | 7.5 | - | nH |
| Source-d | rain diode | | | | | |
| V_{SD} | source-drain voltage | I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u> | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | I _S = 20 A; dI _S /dt = -100 A/μs; | - | 76 | - | ns |
| Q _r | recovered charge | V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C | - | 282 | - | nC |

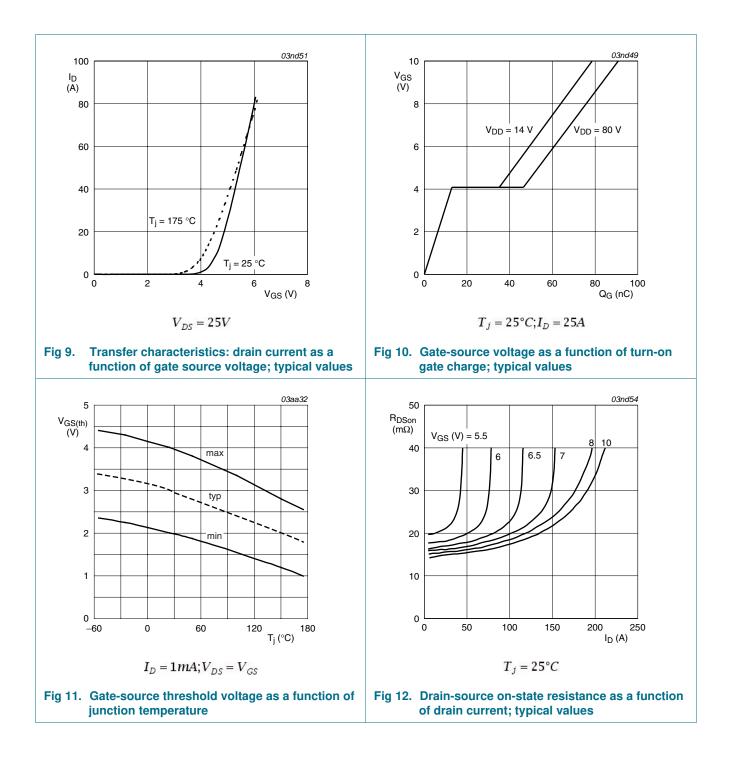
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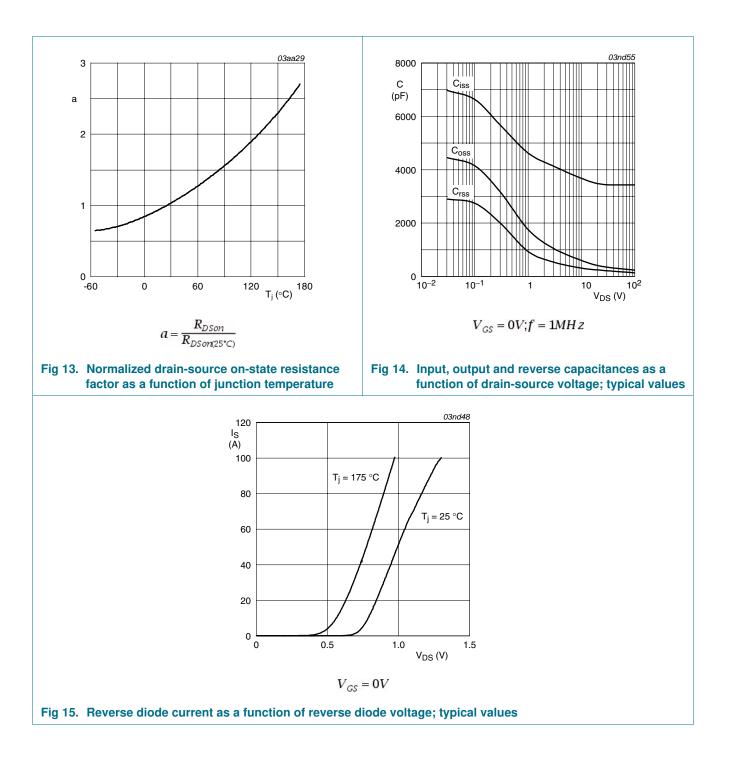
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7. Package outline

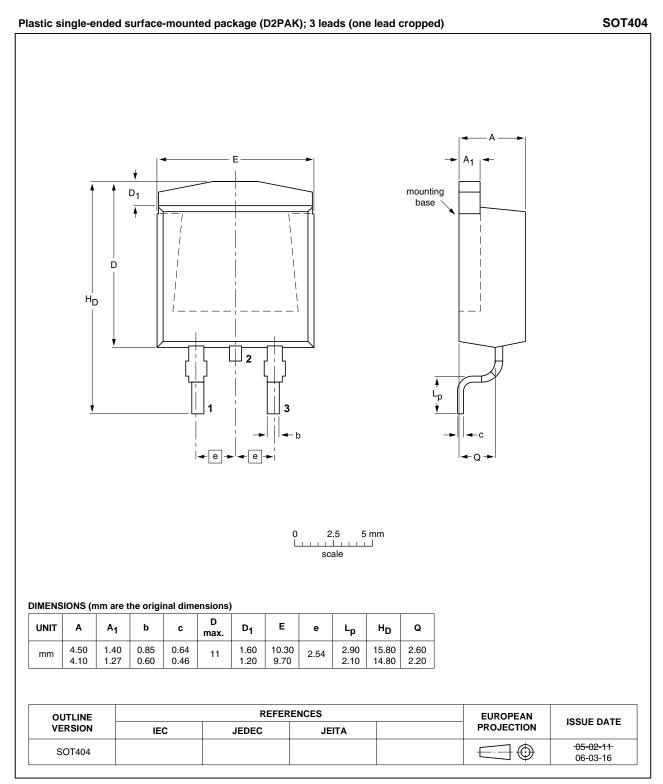


Fig 16. Package outline SOT404 (D2PAK)

BUK7620-100A Product data sheet

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8. Revision history

| Table 7. | Revision history | | | | |
|----------------|-------------------------|---------------------------------|--------------------------|--------------------|-----------------------------|
| Documen | t ID | Release date | Data sheet status | Change notice | Supersedes |
| BUK7620- | 100A v.2 | 20110202 | Product data sheet | - | BUK7520_7620_100A-01 |
| Modifications: | | guidelines c | of NXP Semiconductors. | 5 | omply with the new identity |
| | | 0 | have been adapted to the | 1 3 | |
| | | Type number | er BUK7620-100A separa | ated from data she | et BUK7520_7620_100A-01. |
| BUK7520 | _7620_100A-01 | 20010205 | Product specification | - | - |

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| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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